



AP1000A

SILICON PIN DIODE

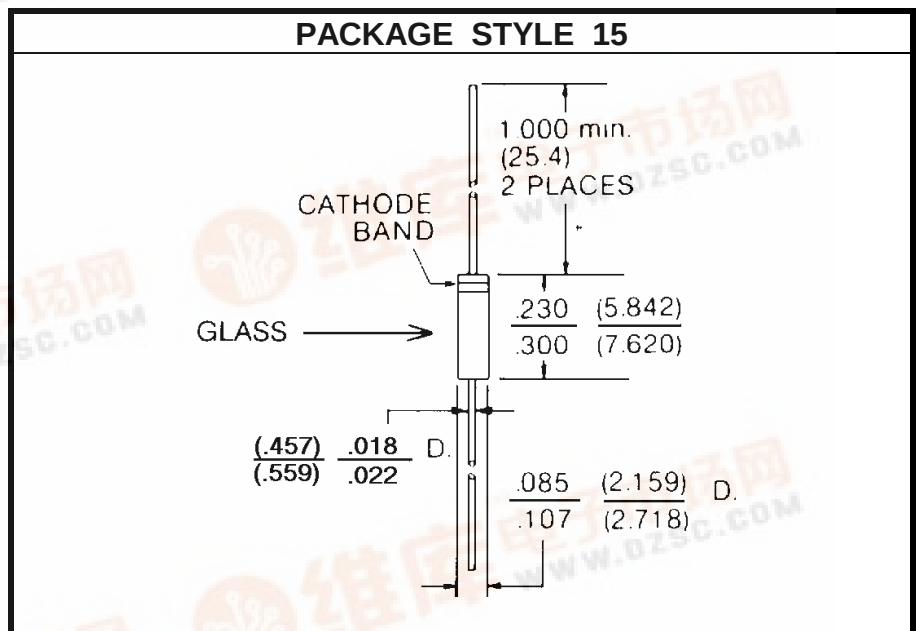
DESCRIPTION:

The **AP1000A** is a Diffused Epitaxial Silicon PIN Diode.

MAXIMUM RATINGS

I_C	100mA
V_{CE}	100 V
P_{DISS}	500 mW @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+150^\circ C$
T_{STG}	$-65^\circ C$ to $+175^\circ C$
θ_{JC}	$50^\circ C/W$
T_{SOLD}	5.0 Sec./ $200^\circ C$

PACKAGE STYLE 15



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	$I_R = 10 \mu A$	100			V
C_J	$V_R = 6.0 V$ $f = 1.0 MHz$			0.05	pF
R_s	$I_F = 20 mA$ $f = 1.0 GHz$ $I_F = 100 mA$			2.6 2.0	Ohms
T_L	$I_F = 10 mA$ $I_R = 6.0 mA$		100		nS
T_s	10%-90% / 90%-10%			10	nS
C_p	$f = 1.0 MHz$		0.15		pF
L_s			2.5		nH